



60V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D Tc = +25°C
60V	18mΩ @ V _{GS} = 10V	17.1A
	24.5mΩ @ V _{GS} = 4.5V	14.7A

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

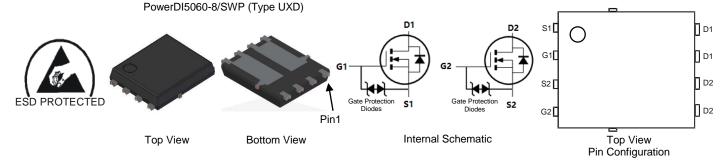
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Wireless Charging
- DC-DC Converters
- Power Management

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)



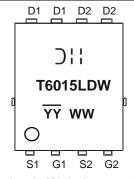
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6015LPDW-13	PowerDI5060-8/SWP (Type UXD)	2500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ H = Manufacturer's Marking

T6015LDW = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 20 = 2020)

WW = Week Code (01 to 53)

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Document number: DS42174 Rev. 3 - 2



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage		V_{GSS}	±16	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_C = +25$ °C $T_C = +70$ °C	lp	17.1 13.7	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 5) $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		Ι _D	9.4 7.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	68	Α	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	17	Α
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)		Ism	68	Α
Avalanche Current L = 0.1mH		I _{AS}	20.7	Α
Avalanche Energy L = 0.1mH		Eas	21.4	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	52.1	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	7.9	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	15.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

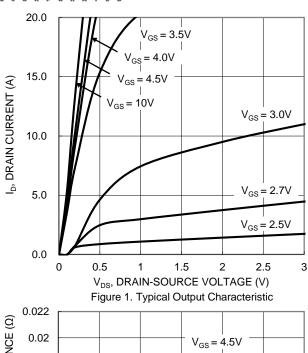
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	V _G S = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			•		•	•	
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	13.7	18	mΩ	V _G S = 10V, I _D = 10A	
Static Drain-Source On-Resistance	Rds(on)	_	18.3	24.5	11177	V _G S = 4.5V, I _D = 6A	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		808	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		279	_	pF		
Reverse Transfer Capacitance	Crss	_	30	_			
Gate Resistance	Rg		1.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	8.6	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	15.7	_	~_	201/ 1- 404	
Gate-Source Charge	Qgs		2.9	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Q _{gd}		3.4	_			
Turn-On Delay Time	td(on)		7.5	_			
Turn-On Rise Time	tR	_	2.7	_		$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t _{D(OFF)}		17.4	_	ns	$R_G = 6\Omega$, $I_D = 10A$	
Turn-Off Fall Time	tr		8.9	_			
Reverse Recovery Time	trr		26.7	_	ns	1 404 11/11 4004/	
Reverse Recovery Charge	Qrr	1	16.2	_	nC	I _F = 10A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





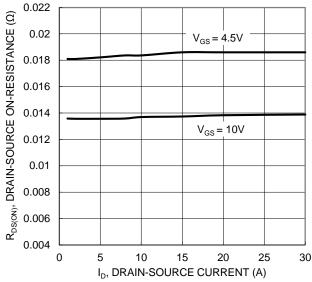


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

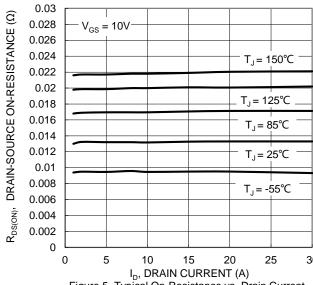


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

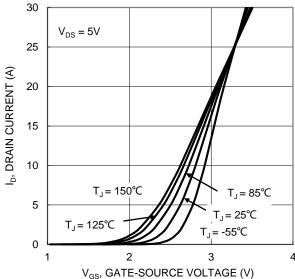


Figure 2. Typical Transfer Characteristic

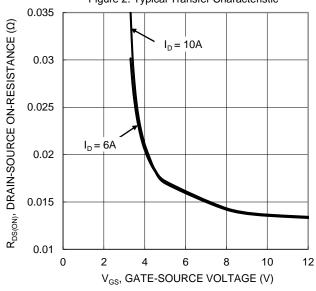
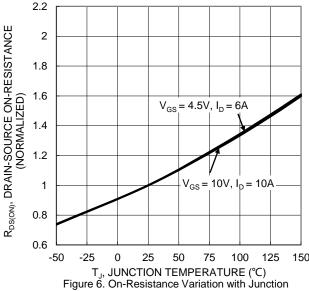


Figure 4. Typical Transfer Characteristic



Temperature



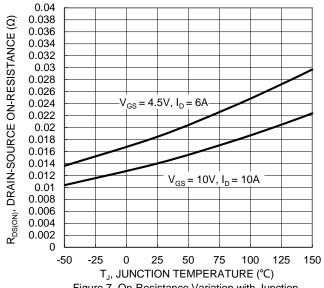
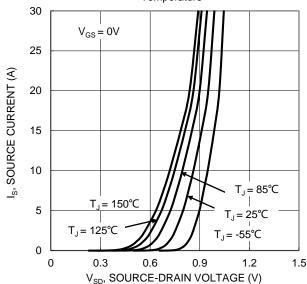


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

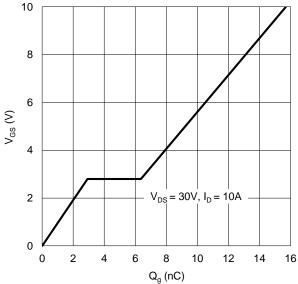


Figure 11. Gate Charge

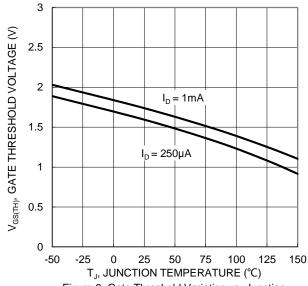
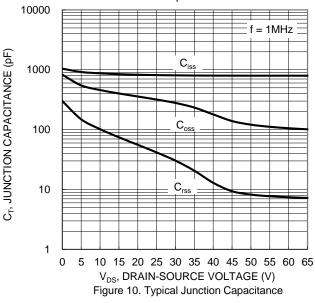


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000
Ros(ON)
Limited

100

ROS(ON)
Limited

100

P_W = 1µs

P_W = 10ms
P_W = 10ms
P_W = 10ms
P_W = 10ms
P_W = 10us
P_W



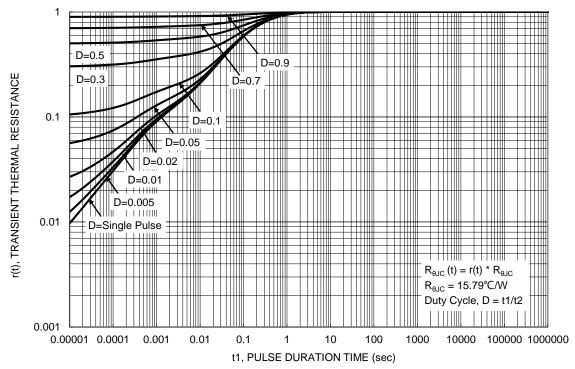


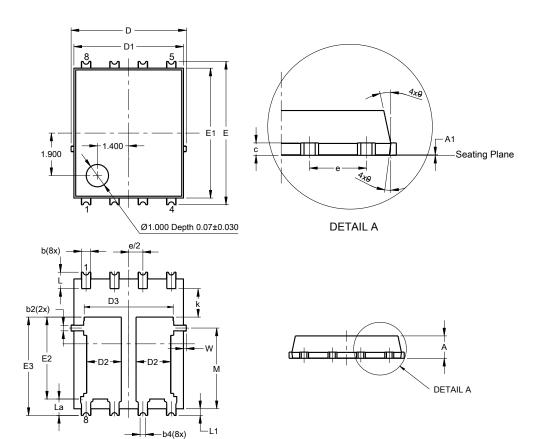
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)

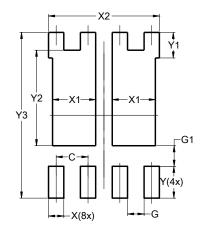


PowerDI5060-8/SWP (Type UXD)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
C	0.230	0.330	0.277		
D	5	5.15 BSC			
D1	4.70	5.10	4.90		
D2	1.46	1.66	1.55		
D3	3.78	4.18	3.98		
Е	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC)		
k	1.05		-		
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
M	3.205	4.005	3.605		
W	0.025	0.225	0.125		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	1.720		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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